

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE

2SC4793

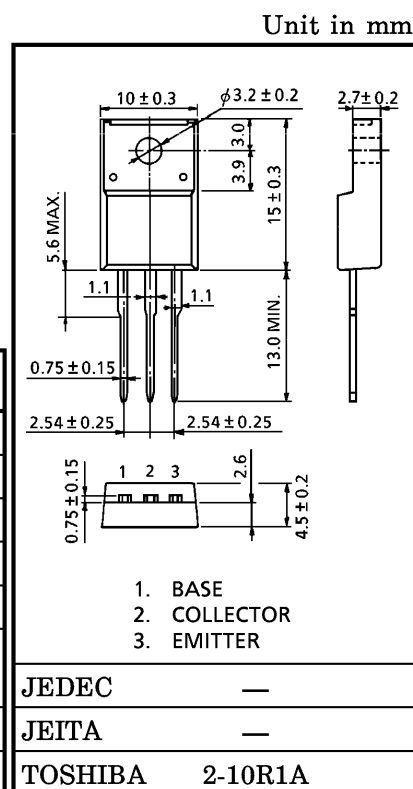
POWER AMPLIFIER APPLICATIONS

DRIVER STAGE AMPLIFIER APPLICATIONS

- High Transition Frequency : $f_T = 100\text{MHz}$ (Typ.)
- Complementary to 2SA1837

MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	230	V
Collector-Emitter Voltage	V_{CEO}	230	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Base Current	I_B	0.1	A
Collector Power Dissipation	$T_a = 25^\circ\text{C}$	P_C 2.0	W
	$T_c = 25^\circ\text{C}$	20	
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$



Weight : 1.7g (Typ.)

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 230\text{V}, I_E = 0$	—	—	1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$	—	—	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 10\text{mA}, I_B = 0$	230	—	—	V
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 100\text{mA}$	100	—	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$	—	—	1.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 5\text{V}, I_C = 500\text{mA}$	—	—	1.0	V
Transition Frequency	f_T	$V_{CE} = 10\text{V}, I_C = 100\text{mA}$	—	100	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	—	20	—	pF

